Nch 600V 46A Power MOSFET

V _{DSS}	600V
R _{DS(on)} (Max.)	81mΩ
I _D	±46A
P _D	130W

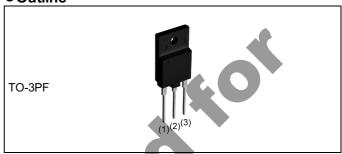
Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be ±30V.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

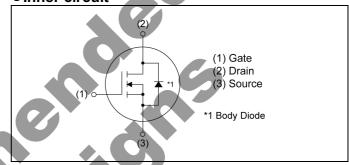
Application

Switching Power Supply

Outline



•Inner circuit



<u> </u>	ing opcomoducions	
	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
Туре	Basic ordering unit (pcs)	360
	Taping code	C8
	Marking	R6046ANZ

● Absolute maximum ratings (T_a = 25°C, unless otherwise specified)

Parameter	Symbol	Value	Unit	
Drain - Source voltage		V_{DSS}	600	V
Continuous drain augrant	T _C = 25°C	I _D *1	±46	Α
Continuous drain current	T _C = 100°C	I _D *1	±22.4	Α
Pulsed drain current		I _{DP} *2	±115	Α
Gate - Source voltage		V_{GSS}	±30	V
Avalanche current, single pulse		I _{AS} *3	AS*3 23	
Avalanche energy, single pulse		E _{AS} *3	142	mJ
Avalanche energy, repetitive		E _{AR} *4	10	mJ
Power dissipation (T _c = 25°C)		P _D	130	W
Junction temperature		T _j	150	°C
Operating junction and storage temperature range		T _{stg}	-55 to +150	°C
Reverse diode dv/dt		dv/dt	15	V/ns

Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	d∨/dt	$V_{DS} = 480V, I_{D} = 46A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
raianetei	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R _{thJC}	-	-	0.96	°C/W
Thermal resistance, junction - ambient	R _{thJA}		-	40	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}		1	265	°C

● Electrical characteristics (T_a = 25°C)

o 1 ,	0		COIG				
●Electrical characteristics (T _a	= 25°C)				5		
					Values		11.7
Parameter	Symbol	Conditi	ons	Min.	Тур.	Max.	Unit
Drain - Source breakdown voltage	V _{(BR)DS\$}	$V_{GS} = 0V, I_D =$	1mA	600	1	ı	٧
Drain - Source avalanche breakdown voltage	V _{(BR)DS}	$V_{GS} = 0V, I_D =$: 23A	ı	700	ı	V
Zero gate voltage drain current	I _{DSS}	V_{DS} = 600V, V T_j = 25°C T_j = 125°C	_{'GS} = 0V		0.1	100 1000	μΑ
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 30V, V$	_{DS} = 0V	-	-	±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} = 10V, I _D	= 1mA	2.5	-	4.5	V
Static drain - source on - state resistance	R _{DS(on)} *6	$V_{GS} = 10V, I_D$ $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$	= 23A	-	65 140	81	mΩ
Gate resistance	R_G	f = 1MHz, ope	n drain	-	1.8	-	Ω

● Electrical characteristics (T_a = 25°C)

Parameter	Cymah ol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Forward Transfer Admittance	Y _{fs} *6	V _{DS} = 10V, I _D = 23A	19	33	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	ı	6000		
Output capacitance	C _{oss}	V _{DS} = 25V	-	3900	5)	pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	90	_	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V,		188	-	ړ
Effective output capacitance, time related	C _{o(tr)}	V _{DS} = 0V to 480V		640	-	pF
Turn - on delay time	t _{d(on)} *6	V _{DD} ≈ 300V, V _{GS} = 10V	-	60	-	
Rise time	t _r *6	I _D = 23A		130	-	
Turn - off delay time	t _{d(off)} *6	R _L ≃ 13Ω		230	460	ns
Fall time	t _f *6	$R_G = 10\Omega$		100	200	

● Gate charge characteristics (T_a = 25°C)

Parameter	Cymbol	Symbol Conditions -		Values		
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Total gate charge	Q_g^{*6}	$V_{DD} \simeq 300V$	-	150	1	
Gate - Source charge	Q _{gs} *6	I _D = 46A	-	35	1	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	55	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 300V$, $I_D = 46A$	-	6.2	ı	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw ≤ 10µs, Duty cycle ≤ 1%

^{*3} L \simeq 500 μ H, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25°C

^{*4} L $^{\sim}$ 500 μ H, V $_{DD}$ = 50V, R $_{G}$ = 25 Ω , starting T $_{j}$ = 25 $^{\circ}$ C, f = 10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

● Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Darameter	Cy made al	Canditions	Values			1.114
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Continuous forward current	I _S *1	T - 25°0	-	-	46	Α
Pulse forward current	I _{SP} *2	T _C = 25°C	-	-	115	A
Forward voltage	V _{SD} *6	$V_{GS} = 0V, I_{S} = 46A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		-	692	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 46A di/dt = 100A/µs		15.1	-	μC
Peak reverse recovery current	I _{rrm} *6	αι/αι – 100/4μ3	(-7)	43.6	-	Α
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C).	940	-	A/µs

● Typical transient thermal characteristics

Symbol	Value	Unit
R _{th1}	0.0341	
R _{th2}	0.266	k/W
R _{th3}	1.24	4

Symbol	Value	Unit
C _{th1}	0.0112	
C _{th2}	0.133	Ws/K
C_{th3}	1.27	

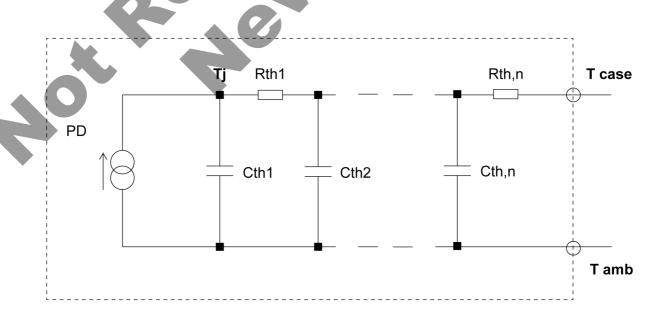


Fig.1 Power Dissipation Derating Curve

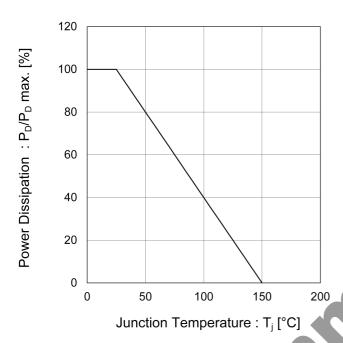


Fig.2 Maximum Safe Operating Area

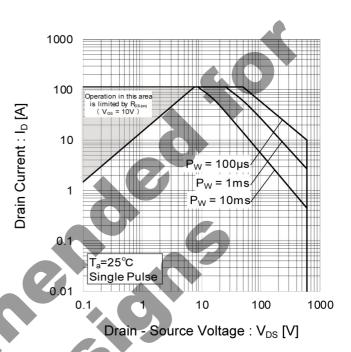
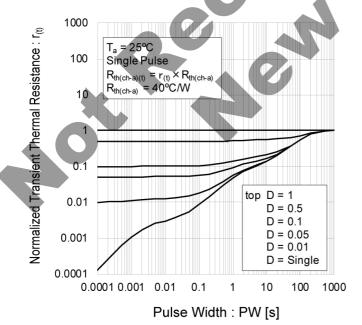


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



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Fig.4 Avalanche Current vs. Inductive Load

Fig.5 Avalanche Power Losses

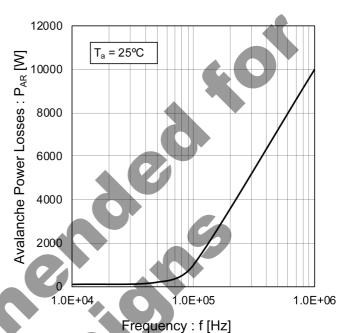


Fig.6 Avalanche Energy Derating Curve vs. Junction Temperature

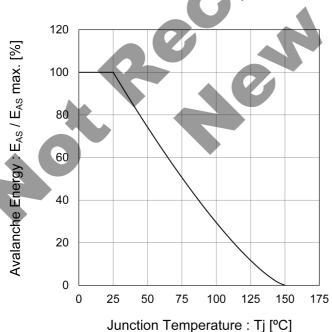


Fig.7 Typical Output Characteristics(I)

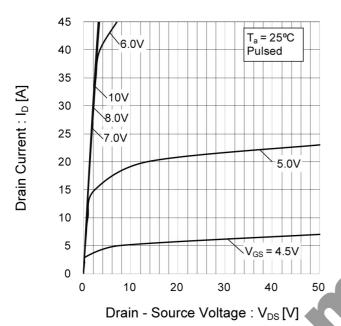
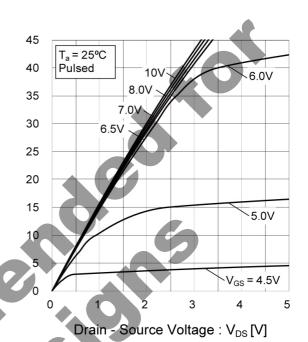


Fig.8 Typical Output Characteristics(II)



Drain Current : I_D [A]

Fig.9 Tj = 150°C Typical Output
Characteristics (I)

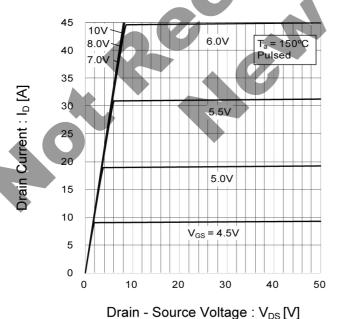
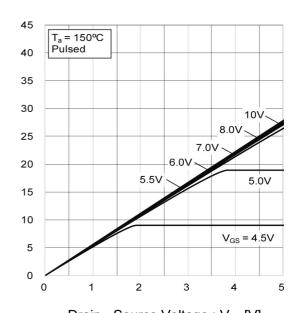


Fig.10 Tj = 150°C Typical Output Characteristics (II)



 $Drain - Source\ Voltage: V_{DS}[V]$

Drain Current : I_D [A]

Fig.11 Breakdown Voltage vs. Junction Temperature

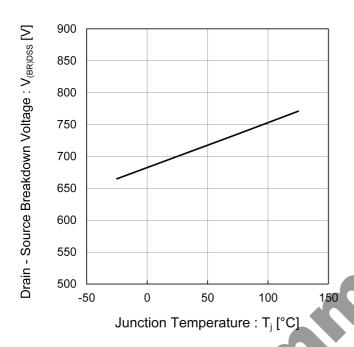


Fig.12 Typical Transfer Characteristics

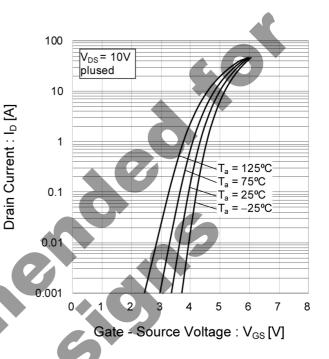


Fig.13 Gate Threshold Voltage vs. Junction Temperature

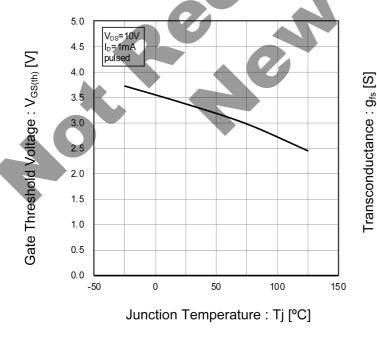


Fig.14 Transconductance vs. Drain Current

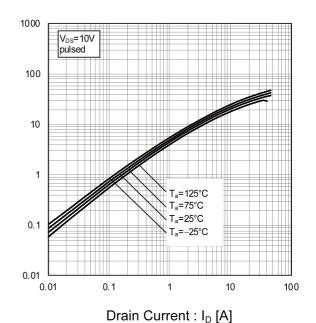


Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

Static Drain - Source On-State Resistance 150 $V_{DS} = 10V$ 140 plused 130 120 110 $R_{DS(on)}$ [m Ω] = 46A 100 = 23A90 80 70 60 50 40 30 10 12 14 16 18 20 0 2 Gate - Source Voltage : V_{GS} [V]

Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature

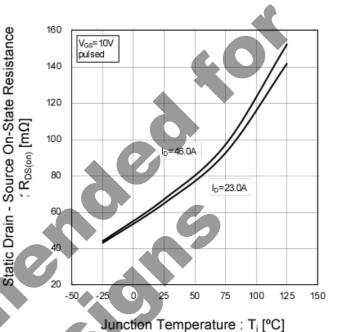
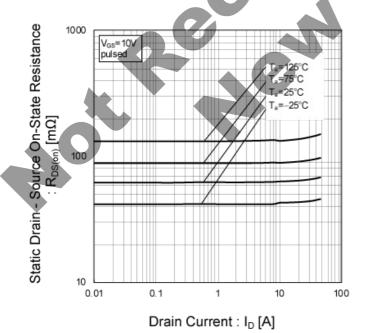
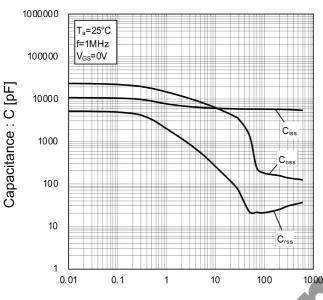


Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



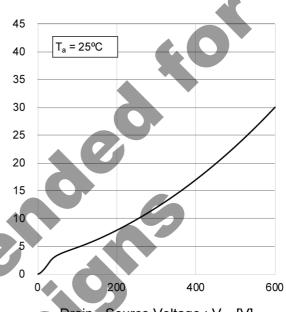
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Fig.18 Typical Capacitance vs. Drain - Source Voltage



Drain - Source Voltage : V_{DS} [V]

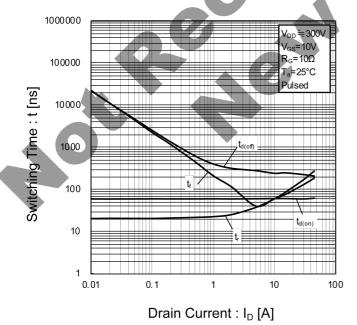
Fig.19 Coss Stored Energy



Drain - Source Voltage : V_{DS} [V]

Fig.21 Dynamic Input Characteristics

Fig.20 Switching Characteristics



Gate - Source Voltage : V_{GS} [V]

Coss Stored Energy : E $_{
m oss}$ [μ J]

T_a=25°C V_{DD}=300V I_D=46A Pulsed

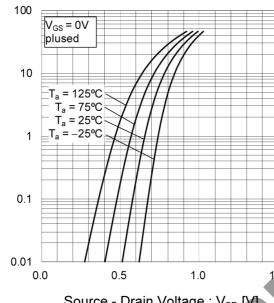
0 10 20 30 40 50 60 70 80 90 100110120130140150

Total Gate Charge: Qg [nC]

Inverse Diode Forward Current : Is [A]

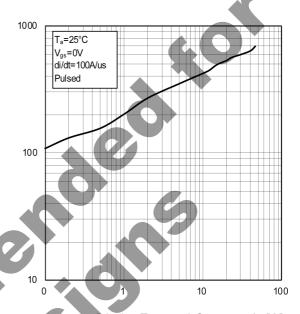
• Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage



Source - Drain Voltage : V_{SD} [V]

Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



Inverse Diode Forward Current : Is [A]



Reverse Recovery Time : t_{rr} [ns]

Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

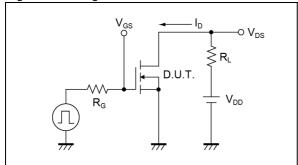


Fig.2-1 Gate Charge Measurement Circuit

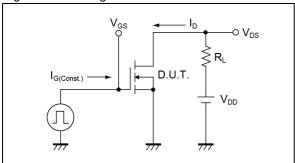


Fig.3-1 Avalanche Measurement Circuit

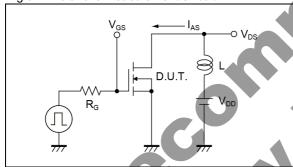


Fig.4-1 dv/dt Measurement Circuit

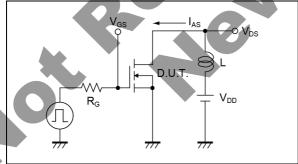


Fig.5-1 di/dt Measurement Circuit

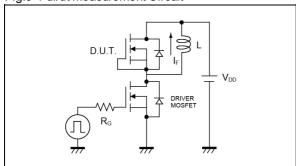


Fig.1-2 Switching Waveforms

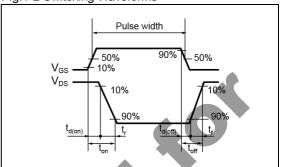


Fig.2-2 Gate Charge Waveform

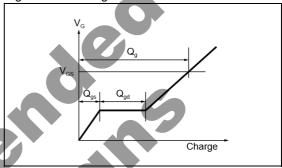


Fig.3-2 Avalanche Waveform

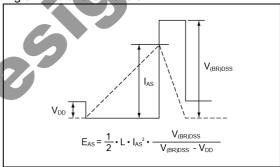


Fig.4-2 dv/dt Waveform

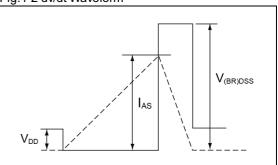
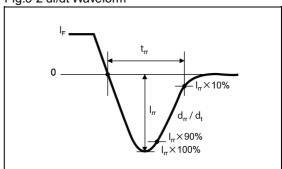
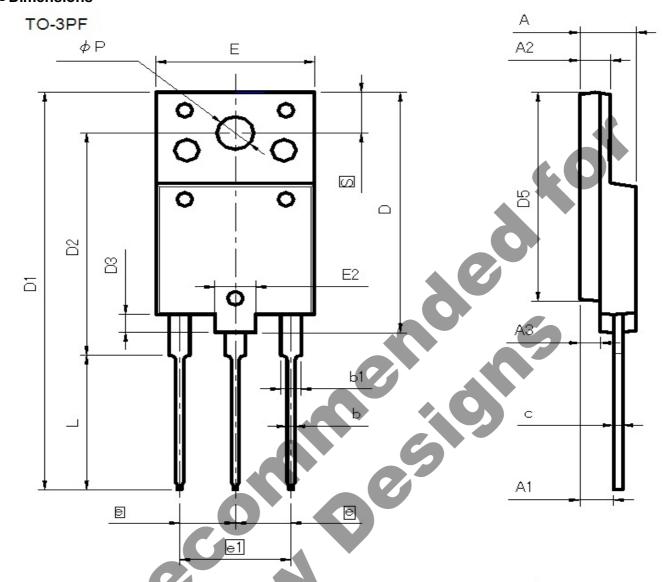


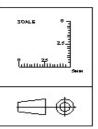
Fig.5-2 di/dt Waveform



Dimensions



0.14	MILIME	ERS	INC	HES
DIM)	MIN	MAX	MIN	MAX
A	5.30	5.70	0.209	0.224
A1	3.10	3.50	0.122	0.138
A2	2.80	3.20	0.11	0.126
A3	1.80	2.20	0.071	0.087
b	0.65	0.95	0.026	0.037
b1	1.80	2.20	0.071	0.087
С	0.80	1.10	0.031	0.043
D	26.30	26.70	1.035	1.051
D1	43.60	44.00	1.717	1.732
D2	24.30	24.70	0.957	0.972
D3	1.80	2.20	0.071	0.087
D4	9.80	10.20	0.386	0.402
D5	22.80	23.20	0.898	0.913
E	15.30	15.70	0.602	0.618
е	5.15	5.75	0.203	0.226
e1	10.60	11.20	0.417	0.441
N	3	1	3	3
L	14.60	15.00	0.575	0.591
φP	3.40	3.80	0.134	0.15
S	4.30	4.70	0.169	0.185



Dimension in mm/inches

Notice

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(Note1) Medical Equipment Classification of the Specific Applications

JAPAN	USA	EU	CHINA
CLASSⅢ	CLASSII	CLASS II b	CLASSII
CLASSIV		CLASSⅢ	

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 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

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This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl2, H2S, NH3, SO2, and NO2
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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многоканальный

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http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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